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Acene-Based Organic Semiconductors for Organic Light-Emitting Diodes and Perovskite Solar Cells

Hong Duc Pham,^a ♦ Hongwei Hu,^b ♦ Fu-Lung Wong,^c ♦ Chun-Sing Lee,^c Wen-Cheng Chen,^c Krishna Feron,^{d,e} Sergei Manzhos,^f Hongxia Wang,^a Nunzio Motta,^a Yeng Ming Lam,^b Prashant Sonar^{a*}

^a Institute of Future Environment and School of Chemistry, Physics and Mechanical Engineering, Queensland University of Technology (QUT), 2 George Street, Brisbane, QLD-4001, Australia.

^b School of Materials Science and Engineering, Nanyang Technological University, 50 Nanyang Avenue, 639798, Singapore.

^c Center of Super-Diamond and Advanced Films, City University of Hong Kong, Kowloon, Hong Kong, P. R. China.

^d CSIRO Energy Centre, NSW-2304, Australia.

^e Centre for Organic Electronics, University of Newcastle, Callaghan, NSW 2308, Australia

^f Department of Mechanical Engineering, Faculty of Engineering, National University of Singapore, Block EA #07-08, 9 Engineering Drive 1, Singapore 117576.

♦ All three authors contributed equally *Email sonar.prashant@qut.edu.au, sonarpm74@gmail.com

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23 ABSTRACT

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24 In this work, three novel acene-based organic semiconductors, including 2,7-
25 bis(trimethylstannyl)naphtho[2,1-*b*:6,5-*b'*]dithiophene (**TPA-NADT-TPA**), 4,4'-(anthracene-
26 2,6-diyl)bis(*N,N*-bis(4-methoxyphenyl)aniline (**TPA-ANR-TPA**) and *N*²,*N*²,*N*⁶,*N*⁶-tetrakis(4-
27 methoxyphenyl)anthracene-2,6-diamine (**DPA-ANR-DPA**), are designed and synthesized for
28 use in organic light-emitting diodes (OLEDs) and perovskite solar cells (PSCs). In OLEDs,
29 the devices based on **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA** showed pure
30 blue, blue green, and green emission, respectively. Also, the maximum brightness of the
31 devices with a turn-on voltage at 3.8 V reached 8682 cd/m² for **TPA-NADT-TPA**, 11180
32 cd/m² for **TPA-ANR-TPA**, and 18600 cd/m² for **DPA-ANR-DPA** respectively. These new
33 materials are also employed as hole transporting materials (HTMs) in inverted PSCs, where
34 they were used without additives. The inverted devices based on these HTMs achieved an
35 overall efficiency of 10.27 % for **TPA-NADT-TPA**, 7.54 % for **TPA-ANR-TPA**, and
36 6.05 % for **DPA-ANR-DPA** under identical condition (AM 1.5G and 100 mW cm⁻²). While
37 the PSCs with **TPA-NADT-TPA** as HTM achieved the highest efficiency, the **DPA-ANR-**
38 **DPA** based OLED devices showed the brightest emission and efficiency. Based on the
39 obtained promising performance, it is clear that this molecular design presents a new research
40 strategy to develop materials that can be used in multiple types of devices.

41 42 INTRODUCTION

43 Up to date, a considerable inventory of organic semiconductors, including small molecules
44 and polymers have been synthesized and implemented in various organic electronic devices
45 such as organic solar cells (OSCs or OPV), dye-sensitized solar cells (DSSCs), perovskite
46 solar cells (PSCs), organic field-effect transistors (OFETs), organic light-emitting diodes
47 (OLEDs) and so on. These materials can be categorized into two groups based on their
48 applications. One includes a single organic semiconducting material that can be designed for
49 a single specific application. There is rich literature in which such materials and devices have
50 been reported. The other group can be defined as multipurpose materials where a single
51 molecule can be used in several types of devices. It has been widely reported that materials
52 developed for OFET devices can also be used successfully for OPV and exhibit very high
53 performance in both types of devices.¹⁻³ Currently, there are few studies relative to organic
54 semiconducting materials which can be used for dual application such as OSCs and PSCs.⁴⁻⁷

55 However, there are hardly any studies on organic semiconductors which can be used for a
56 dual application in OLEDs and PSCs. Herein, we are reporting the use of a single type of
57 materials for two different types of devices, namely, OLED and PSC.

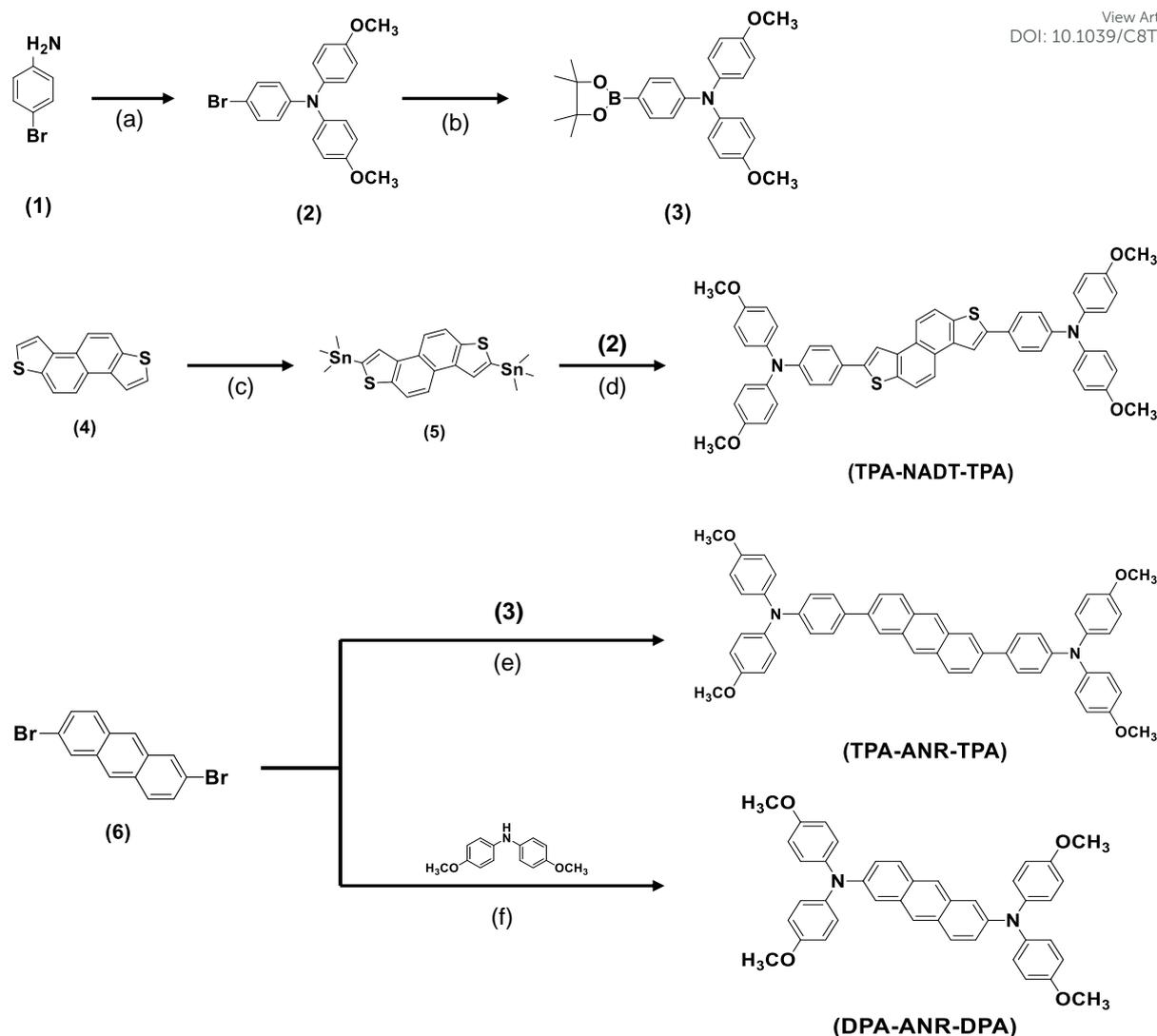
58 The application of OLED in TVs, smartphones, digital cameras, and so on⁸⁻¹¹ has
59 been very successful commercially because this technology guarantees high-energy
60 efficiency and pure bright colours; it allows large area processing and is suitable for flexible
61 displays.¹²⁻¹⁴ As a consequence, highly efficient clear red, blue, and green coloured OLED
62 devices have been developed. However, there is still great demand to reduce the cost and
63 further improve performance of such devices for the production of state of the art large area
64 processable light emitting materials. This task requires molecular engineering to develop
65 novel organic semiconductors.¹⁵⁻¹⁸ High performance red/orange emissive materials already
66 exist in the market, but for pure blue/green emission, low cost materials still remain a critical
67 challenge, particularly in terms of high efficiency, easy availability, and colour purity.^{11, 19, 20}

68 One of the promising optoelectronic applications of organic semiconductors is to
69 design low cost high performance charge transporting materials for PSCs. Perovskite based
70 solar harvesting technology has gained significant attention and became one of the hot topics
71 in both academic and industrial research. The fast growth of PSC technology is due to
72 astonish improvements in power conversion efficiency (PCE) within the last few years (from
73 3.8 % to 22.7 % in seven years).²¹ Basically, the device configuration of PSCs is categorized
74 into conventional (n-i-p) and inverted (p-i-n) types. Compared to the conventional one, the
75 inverted architectures provide many significant benefits. First, the inverted devices are
76 fabricated by using low-temperature solution-processing techniques and thus can be simply
77 employed on flexible substrates, leading to very promising large-area production of these
78 devices.²²⁻²⁵ Second, they can avoid high-temperature instability and large hysteresis issues,
79 which impede practical application of PSCs.²⁵⁻²⁷ Up to date, several research groups have
80 developed numerous organic semiconductors that serve as hole transporting layer (HTL) of
81 inverted PSC layouts. This layer is critical to achieve very high open circuit voltage (V_{oc}) and
82 PCE in the inverted PSCs.^{28, 29} Furthermore, in addition to hole transport ability after exciton
83 dissociation, the HTL plays a key role to protect the active perovskite layer from
84 moisture/oxygen ingress and electrode penetration.^{30, 31} Currently, the champion efficiencies
85 of inverted PSCs exhibited roughly 19.4% and 18.1% by using poly[bis(4-phenyl)(2,4,6-
86 trimethylphenyl)amine] (PTAA)³² and poly(3,4-ethylenedioxythiophene : polystyrene
87 sulfonate) (PEDOT : PSS)³³ as the hole transporting materials (HTMs), respectively.

88 Unfortunately, the PTAA polymer is extremely costly, being about 50 times the price of gold
89 whereas PEDOT:PSS is hydrophilic and of a strong acidic nature which reduces the device's
90 long-term stability.^{24, 34, 35} In addition to the above limitations, molecular weight of polymers
91 varies batch-to-batch, which may further affect the performance of the device. Compared to
92 polymeric semiconductors based HTMs, small molecules, which present several intrinsic
93 advantages such as good yield,⁵ defined molecular structure,³⁶ tunable energetics³⁷ and good
94 batch-to-batch reproducibility,^{5, 36} can alleviate these limitations. One of the most well-known
95 small molecular HTMs is 2,2',7,7'-tetrakis(*N,N*'-di-*p*-methoxyphenylamino)-9,9'-
96 spirobiorene (Spiro-OMeTAD). Although Spiro-OMeTAD based devices achieved a
97 remarkable performance of 20.8%,³⁸ there are significant drawbacks of Spiro-OMeTAD
98 including high cost, multistep synthesis and cell stability.³⁹ Spiro-OMeTAD usually requires
99 salt type additives to enhance the conductivity in order to achieve high performance of the
100 device. Due to the use of salts as additives, the PSC devices are vulnerable to the
101 environmental stability, and performance degrades rapidly.^{31, 40} These bottlenecks can be
102 addressed by developing new generation HTMs via molecular design.

103 In the present work, we are reporting three novel small molecules, namely 2,7-
104 bis(trimethylstannyl)naphtho[2,1-*b*:6,5-*b'*]dithiophene (**TPA-NADT-TPA**), 4,4'-(anthracene-
105 2,6-diyl)bis(*N,N*-bis(4-methoxyphenyl)aniline (**TPA-ANR-TPA**) and *N*²,*N*²,*N*⁶,*N*⁶-tetrakis(4-
106 methoxyphenyl)anthracene-2,6-diamine (**DPA-ANR-DPA**) using fused anthracene and
107 naphthodithiophene cores, respectively. The optical, thermal, and electronic properties are
108 characterised experimentally as well as using density functional theory (DFT) calculations.
109 The materials exhibit high thermal stability, good solubility, and high fluorescent efficiency.
110 These materials were used as an active light emitting material in OLED devices and
111 demonstrated promising performance with bright blue-green emission and high brightness.
112 The same materials were also used as hole transporting layers in PSC devices, where they
113 could achieve the highest PCE exceeding 10 % . To the best of our knowledge, these newly
114 developed organic small molecules are reported here for the first time with dual functions as
115 dopants in OLED and pristine hole transporting materials (HTMs) in PSCs.

116



117

118 **Scheme 1.** Synthesis routes of **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA**.

119 Reagent and conditions: (a) 1-iodo-4-methoxybenzene, KOH, CuCl, 1,10-phenanthroline

120 monohydrate, toluene, 120 °C, overnight; (b) bis(pinacolato)diboron, KOAc, Pd(dppf)Cl₂,121 DMF, 80 °C, 12 h; (c) n-BuLi, THF, Me₃SnCl, -78 °C, 12 h; (d) 2,7-122 bis(trimethylstannyl)naphtho[2,1-*b*:6,5-*b'*]dithiophene, DMF, Pd(PPh₃)₄, 110 °C, 48 h; (e) 2M123 K₂CO₃, toluene, Pd(PPh₃)₄, 120 °C, 48 h; (f) Diphenylamine, ^tBu₃P, NaO^tBu, Pd₂(dba)₃,

124 Toluene, 110 °C, 48 h.

125

126

127 RESULTS AND DISCUSSIONS

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128 Molecular Design and Synthesis.

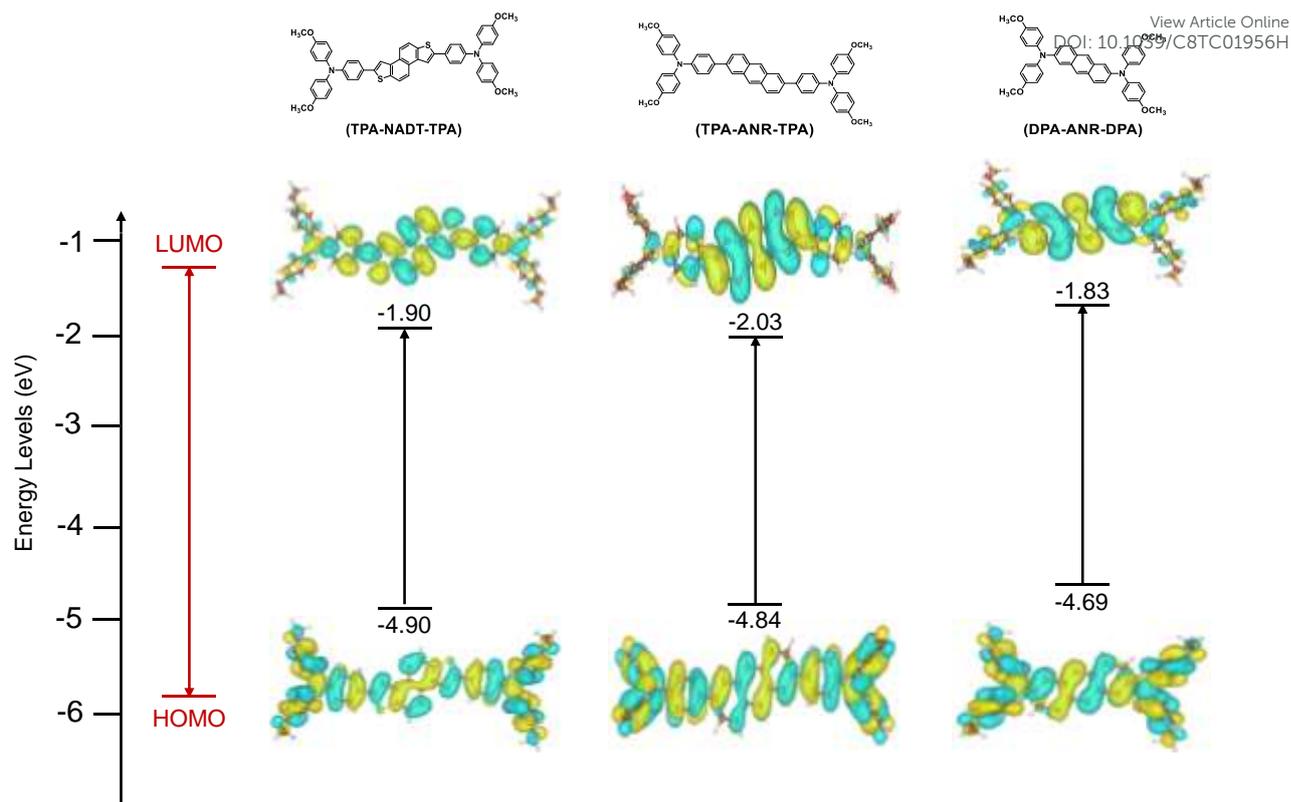
129 Acene cores have been used successfully for synthesizing various classes of organic
130 semiconductors for a wide range of applications including OFETs⁴¹⁻⁴³, OLEDs⁴⁴⁻⁴⁶, PSCs,^{47,}
131 ⁴⁸ and OPV⁴⁹⁻⁵². Due to their fused aromatic structure and planar nature, acenes can be
132 considered as a potent class of conjugated building blocks for constructing new high
133 performance organic semiconductors. In this work, we have used two simply fused cores
134 based on fused phenylene aromatic, “anthracene”, and naphthalene fused with thiophene,
135 “naphtho[1,2-*b*:5,6-*b'*]dithiophene”, respectively. The rationale for the choice of anthracene
136 (ANR) and naphtho[1,2-*b*:5,6-*b'*]dithiophene (NADT) cores is due to their planar nature.
137 Planar groups are extremely beneficial for organic electronics because they can provide high
138 charge-carrier mobility and ultimately high performance.⁵³⁻⁵⁶ Additionally, their fused nature
139 is significant for better π - π stacking due to large orbital overlap. Herein, ANR group has been
140 rationally selected due to its key important features such as strong emission and high charge
141 carrier mobility.⁴⁶ Besides the ANR core, we have also used NADT fused core due to its
142 more extended conjugation than ANR. Fusion of two thiophene rings with naphthalene
143 makes it more electron rich and highly planar. NADT would be an ideal core to compare with
144 ANR core because both of these units possess high charge carrier mobility and high
145 performance in devices.^{57, 58} Furthermore, the attachment of thiophene moieties in NADT
146 structure has been shown to improve OLEDs^{59, 60}, OSCs,^{56, 61} and PSCs^{25, 62} performance.
147 ANR and NADT groups were selected as cores whereas triphenylamine (TPA) and
148 diphenylamine (DPA) moieties are selected as end-capping groups in order to study their
149 effect on the device performance. The TPA unit has been widely used in OSCs, DSSCs and
150 PSCs^{36, 63} owing to its 3D propeller design, strong electron-donating and transporting
151 capabilities and amorphous structure forming ability.^{64, 65} Its derivatives are also implemented
152 widely as hole-transporting or light-emitting materials in OLEDs.⁶⁴⁻⁷² However, the long
153 intermolecular distance of the non-planar TPA may lead to low hole mobility. Thus, DPA
154 groups are introduced at the end of ANR and NADT cores for comparison with TPA.
155 Although the DPA group is a weaker electron donor compared to TPA, DPA derivatives have
156 demonstrated high efficiencies in OSCs, DSSCs and PSCs.³⁶ However, there are very few
157 studies reporting DPA based derivatives for OLEDs.

158 The synthesis routes of **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA** are depicted in Scheme 1. First, the synthesis of the precursor 4-bromo-*N,N*-bis(4-
159 methoxyphenyl)aniline (2) and 4-methoxy-*N*-(4-methoxyphenyl)-*N*-(4-(4,4,5,5-tetramethyl-
160 1,3,2-dioxaborolan-2-yl)phenyl)aniline (3) followed earlier attempts.^{25, 39} The NADT core
161 (2,7-bis(trimethylstannyl)naphtho[2,1-*b*:6,5-*b*']dithiophene, (5)) was prepared by using
162 naphtho[2,1-*b*:6,5-*b*']dithiophene (4) with trimethyltin chloride (Me₃SnCl) and *n*-butyllithium
163 (n-BuLi) in tetrahydrofuran (THF) solvent at room temperature for 12 h. The target **TPA-**
164 **NADT-TPA** was synthesized by Stille coupling reaction between compound (2) and (5)
165 tetrakis(triphenylphosphine) palladium [Pd(PPh₃)₄] catalyst at 110 °C for 48 h in
166 dimethylformamide (DMF) solvent. Meanwhile, the synthesis of **TPA-ANR-TPA** was based
167 on Suzuki coupling reaction between compound (3) and (6) using tetrakis triphenylphosphine
168 palladium [Pd(PPh₃)₄] catalyst and 2 M K₂CO₃ base at 120 °C for 48 h in toluene solvent.
169 The target compound **DPA-ANR-DPA** was prepared via Buchwald-Hartwig coupling
170 reaction between compound (6) and bis(4-methoxyphenyl)amine using
171 tris(dibenzylideneacetone)dipalladium [Pd₂(dba)₃] catalyst, tri-*tert*-butylphosphine (*t*Bu₃P),
172 and sodium *tert*-butoxide (NaO^{*t*}Bu) at 110 °C for 48 h in toluene solvent. After purification,
173 **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA**'s yield was 38.2 %, 38.3 % and
174 50.2 %, respectively. Their purity was proved by proton and C13 nuclear magnetic resonance
175 (NMR) spectroscopy (Figure S1-S3, ESI†). The molecular weight was confirmed by mass
176 spectroscopy. While the solubility of **DPA-ANR-DPA** was extremely good in most common
177 organic solvents such as chloroform, dichloromethane, and chlorobenzene, **TPA-NADT-**
178 **TPA** and **TPA-ANR-TPA** exhibited lower solubility due to their highly conjugated
179 backbone and rigid chemical structure.
180

181

182 **Ab initio Calculations**

183



184

185 **Fig. 1.** Calculated energy levels of HOMO and LUMO orbital isosurfaces of **TPA-NADT-**
 186 **TPA, TPA-ANR-TPA, and DPA-ANR-DPA.**

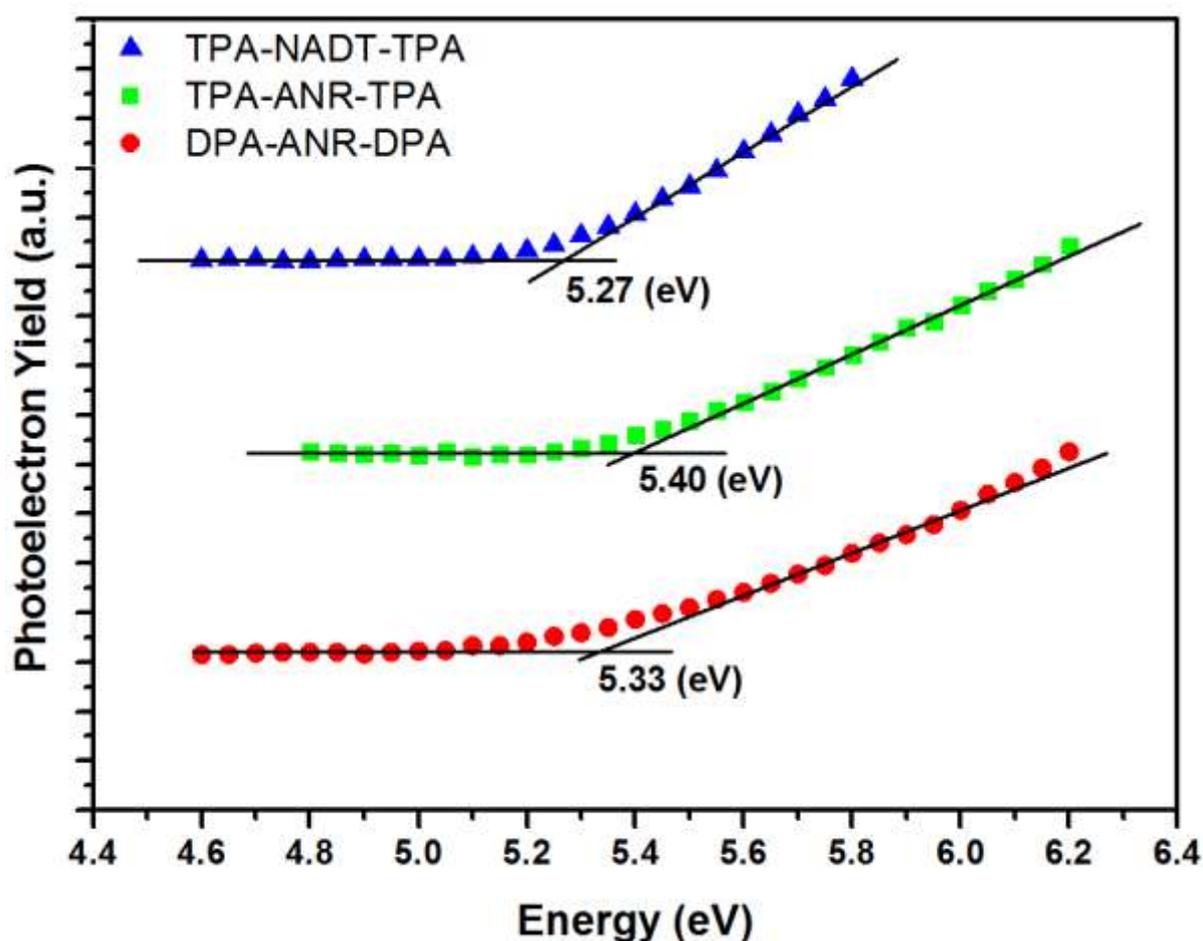
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188 Fig. 1 shows the molecular structures and frontier orbital electron density distributions of the
 189 three new small molecules computed with DFT at the B3LYP/LANL2DZ level with a PCM
 190 model of the chloroform solvent.⁷³⁻⁷⁵ The computed frontier orbital energies, optical
 191 absorption and photoluminescence data are summarized in Table S1 (ESI†). In all three
 192 molecules, both LUMO and HOMO orbitals are delocalized over the entire aromatic system,
 193 which is extremely important for efficient charge transport.⁷⁶ Indeed, the electron distribution
 194 of the LUMO is primarily localized on NADT and ANR cores whereas the HOMO is fully
 195 delocalized over the entire molecules including the end-capping groups, reflecting the
 196 electron-rich nature of TPA and DPA. The calculated HOMO values of **TPA-NADT-TPA,**
 197 **TPA-ANR-TPA,** and **DPA-ANR-DPA** are -4.90, -4.84 and -4.69 eV, respectively; the
 198 LUMO values are -1.90, -2.03 and -1.83 eV, respectively. The theoretical HOMO-LUMO
 199 trend helps understand the effect of end capping groups and the nature of core on the energy
 200 level tuning. Specifically one observes a lower LUMO with TPA vs DPA, which corresponds
 201 to delocalization of the LUMO onto core-adjacent phenyls of the TPA. The DPA unit leads to
 202 a higher HOMO, likely due to steric hindrance with the core of DPA's both phenyl units vs a

203 single core-adjacent unit with TPA. This trend is similar to the experimental results below
204 while the absolute values of HOMO and LUMO differ due to difference in aggregate state
205 and approximations, as expected. We also note that the computed LUMO is higher than the
206 estimate below based on the optical gap as the latter is downshifted due to broadening effects
207 (being determined from the *onset* of absorption).

208 Electrochemical Properties.

209



211 **Fig. 2.** Photoelectron spectroscopy in air (PESA) spectra of three new semiconductors.

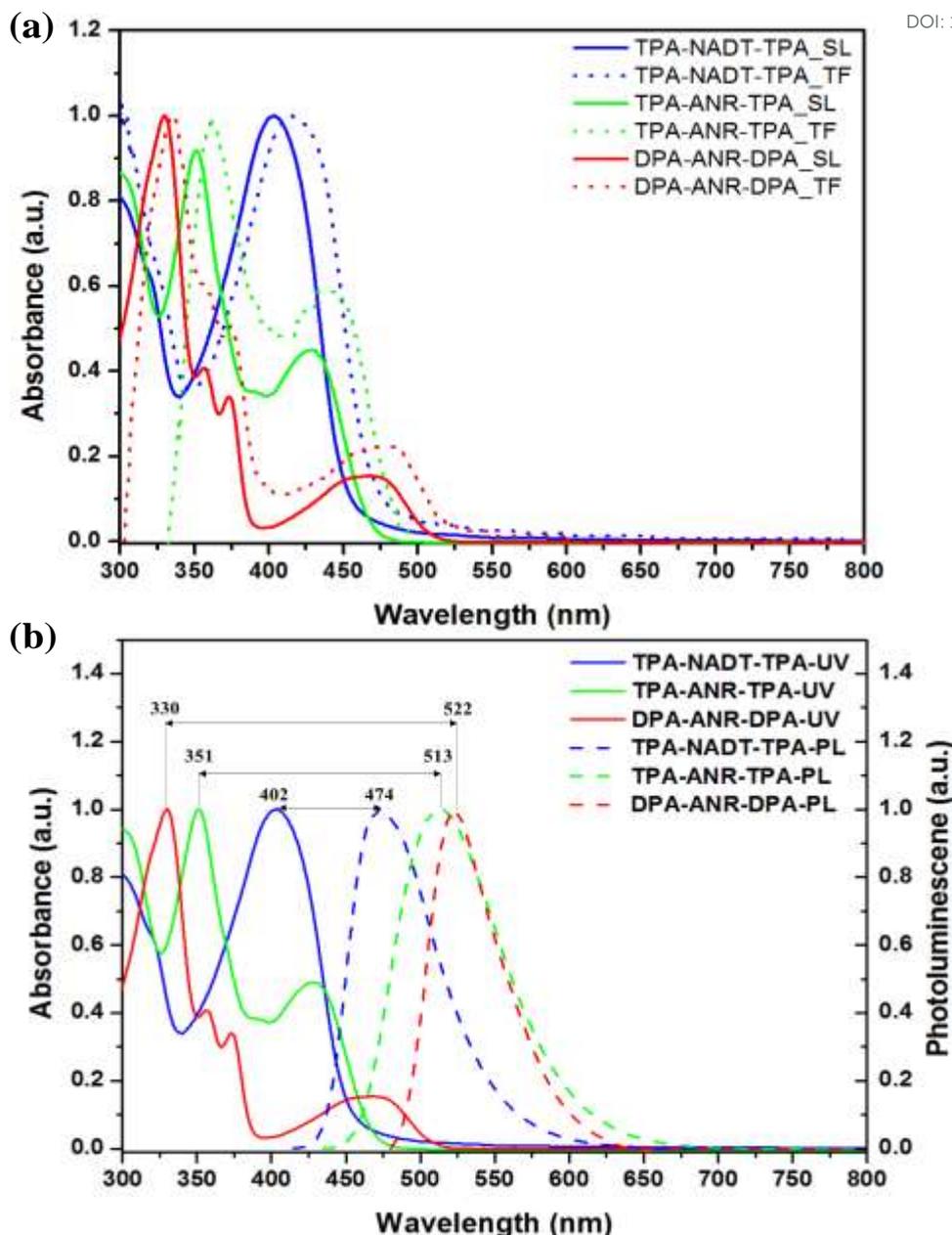
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213 We measured the HOMO energy levels in thin film using photoelectron spectroscopy in air
214 (PESA), whereas, the LUMO values were calculated from the difference between the HOMO
215 values and the optical bandgap. The corresponding data are summarized in Table 1.
216 According to PESA, the HOMO values of **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-**
217 **ANR-DPA** are estimated to be at -5.27, -5.40 and -5.33 eV, respectively. These HOMO

218 values are well matched with that of perovskite ($\text{CH}_3\text{NH}_3\text{PbI}_3$, -5.44 eV) and host (MADN, 5.6 eV) materials, suggesting a good hole injection ability of these new materials. Regarding
219 5.6 eV) materials, suggesting a good hole injection ability of these new materials. Regarding
220 the ANR core, the replacement of end-capping TPA by DPA has affected the HOMO energy
221 level, which proves that TPA units are stronger electron donating ability than DPA ones. This
222 is consistent with the observed red shifts in UV-Vis spectra of both compounds and the trend
223 observed for the energy levels of other HTMs based on ANR core in an earlier report.⁴⁷ From
224 the obtained LUMO values of these compounds, it is clear that they have appropriate value,
225 which is sufficient to block the electron injection due to high-energy offset.

226

227 **Optical Properties.**



228

229 **Fig. 3.** (a) UV-Vis absorption spectra in CF solutions (SL, solid line) and films (TF, dash
 230 line) and (b) Normalised absorption (solid line) and emission spectra (dash line) in CF
 231 solutions of **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA**.

232

233 The optical properties of all newly developed materials characterized by UV-Vis and
 234 photoluminescence spectroscopy respectively. The normalized UV-vis absorption spectra of
 235 **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA** in chloroform (CF) solutions and
 236 solid films are shown in Fig. 3a and the photophysical data are recorded in Table 1. Overall,
 237 there is a similar pattern of the spectra between the thin films and solutions, suggesting that

238 there is no significant crystallization in thin films.⁷⁷ On account of intermolecular interactions
239 in the solid state, the slightly bathochromic shift is observed in the absorption spectra of
240 solid-state films compared to that of solutions. Additionally, the red shift is attributed to the
241 increased π -electron density (π - π^* transitions) of the compound. There is the obvious red-
242 shifted absorption among these compounds in order: **DPA-ANR-DPA** < **TPA-ANR-TPA** <
243 **TPA-NADT-TPA** which could be ascribed to: (a) the DPA unit having the lower electron-
244 donating ability compared to the TPA unit due to number of phenyl groups presents in the
245 structure; (b) the NADT moiety retaining the higher electron-donating ability in comparison
246 to the ANR moiety due to electron rich two thiophene units fused with naphthalene. The
247 optical absorption of these materials exhibit peaks in the ultraviolet (300 – 350 nm) and
248 visible (400 – 500 nm) regions. **TPA-NADT-TPA** displays a strong peak (402 nm) in the
249 visible area and a lower one in the UV region whereas ANR derivatives behave conversely.
250 Compound **DPA-ANR-DPA** unveils absorption maxima at 330 nm for solution and 335 nm
251 for thin film whereas the absorption peaks in solution and thin film of **TPA-ANR-TPA** are
252 351 and 361 nm, respectively. Indeed, the optical band gaps of **TPA-NADT-TPA**, **TPA-**
253 **ANR-TPA** and **DPA-ANR-DPA** are 2.63, 2.58 and 2.37 eV, respectively, which is
254 determined from the absorption onset wavelength ($E_g^{opt} = 1240 / \lambda_{onset}$) of the corresponding
255 absorption spectrum.

256 The normalized photoluminescence (PL) spectra for these three small molecules were
257 conducted in CF solution and illustrated in Fig. 3b. The emission maximum peaks are found
258 to be 474 nm for **TPA-NADT-TPA**, 513 nm for **TPA-ANR-TPA**, and 522 nm for **DPA-**
259 **ANR-DPA**. Stokes shift, which is defined as the gap between the ground state S_0 and the first
260 excited state S_1 , is calculated from the difference between the maximum of absorption and
261 emission spectra. These compounds possess large Stoke shifts in order: **TPA-NADT-TPA**
262 (72 nm) < **TPA-ANR-TPA** (162 nm) < **DPA-ANR-DPA** (192 nm), indicating that these
263 materials can play dual functionality in both organic light emitting diodes and perovskite
264 solar cells. Note that the measured trend in the PL peaks corresponds to that computed with
265 TD-DFT (Table S1). According to TD-DFT, the peaks are due to LUMO→HOMO
266 transitions; the corresponding HOMO→LUMO transitions in the absorption spectrum
267 correspond in the experimental spectrum to less intense peaks around 475 nm for **DPA-ANR-**
268 **DPA** and around 440 nm for **TPA-ANR-TPA** and to the main peak around 425 nm for **TPA-**
269 **NADT-TPA**.

270

271 **Thermal Properties.**

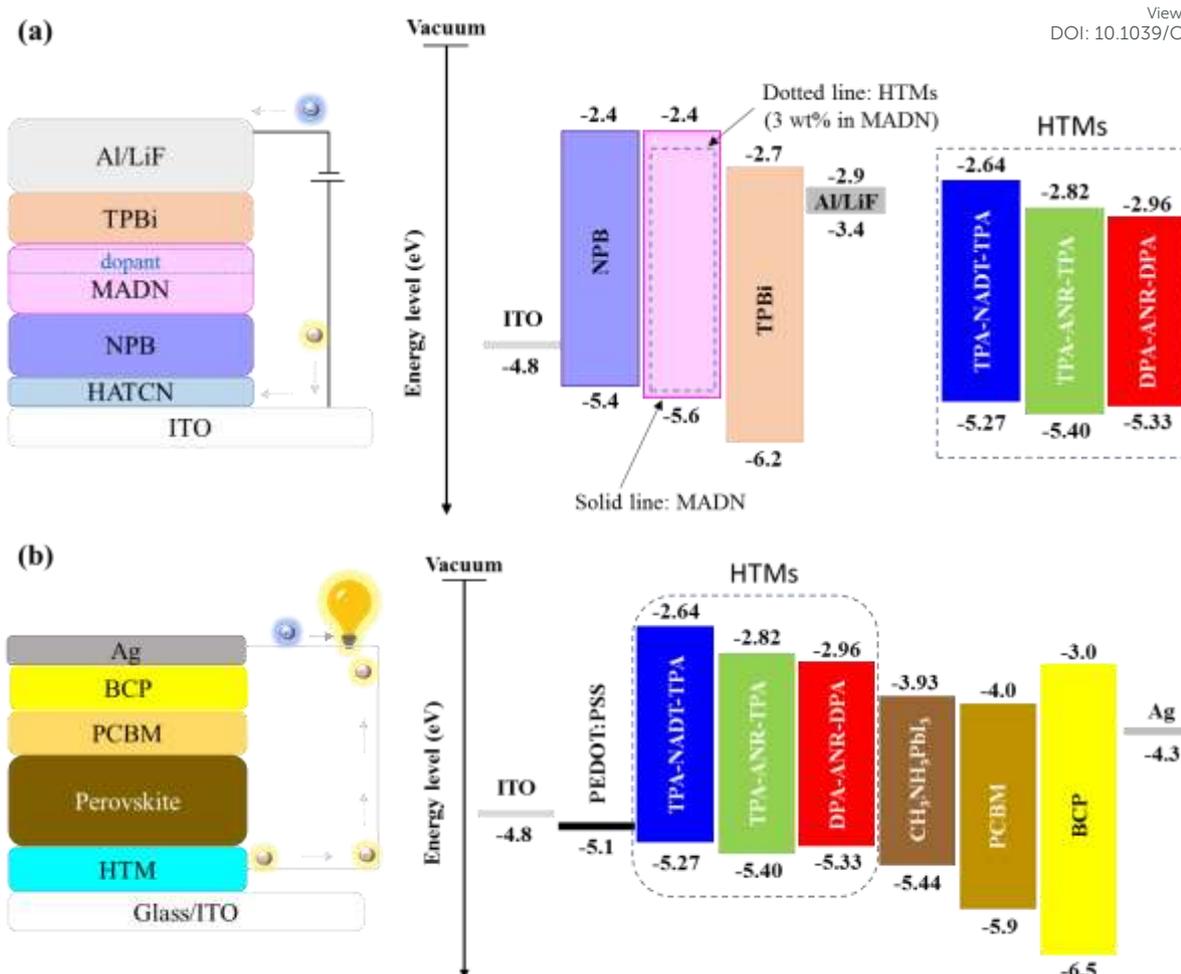
272 In addition to the optical properties, the thermal properties of these new small
 273 molecules were also studied by thermogravimetric analysis (TGA) (Fig. S5, ESI†) and
 274 differential scanning calorimetry (DSC) (Fig. S6, ESI†). Thermal properties of the molecules
 275 are vital in order to study the effect of thermal annealing of the thin film on the performance
 276 of devices. The summarized thermal data are listed in Table 1. According to TGA, these
 277 molecules start to decompose at a temperature above 431 °C for **TPA-NADT-TPA**, 438 °C
 278 for **TPA-ANR-TPA** and 370 °C for **DPA-ANR-DPA**, showing their high thermal stability.
 279 The high and almost identical thermal stability of both **TPA-NADT-TPA** and **TPA-ANR-**
 280 **TPA** is attributed to their rigid molecular pi-conjugated backbone. In addition to this
 281 observation, the DSC results also exhibited a low glass transition temperature (T_g) of 101,
 282 108 and 122 °C for **DPA-ANR-DPA**, **TPA-ANR-TPA**, and **TPA-NADT-TPA**, respectively.
 283 Notably, while **TPA-ANR-TPA** and **TPA-NADT-TPA** do not show a crystallization
 284 temperature (T_c), that of **DPA-ANR-DPA** is observed at 183 °C. The high melting point and
 285 glass transition temperature of all three compounds suggest good heat tolerance for device
 286 fabrication and operation if annealing of thin film is required.

287
288 **Table 1.** Thermal, optical and electrochemical properties of new organic materials.

| HTMs | λ_{\max} [nm] | | $\lambda_{\text{PL}}^{\text{c)}$ [nm] | Stoke shift [nm] | $E_g^{\text{opt d)}$ [eV] | $E_{\text{HOMO}}^{\text{e)}$ [eV] | $E_{\text{LUMO}}^{\text{f)}$ [eV] | T_d [°C] | T_g [°C] | T_m [°C] | T_c [°C] |
|--------------|------------------------|--------------------|--|------------------------|------------------------------|--------------------------------------|--------------------------------------|---------------|---------------|---------------|---------------|
| | Solution ^{a)} | Film ^{b)} | | | | | | | | | |
| TPA-NADT-TPA | 402 | 416 | 474 | 72 | 2.63 | -5.27 | -2.64 | 431 | 122 | 237 | - |
| TPA-ANR-TPA | 351 | 361 | 513 | 162 | 2.58 | -5.40 | -2.82 | 438 | 108 | 217 | - |
| DPA-ANR-DPA | 330 | 335 | 522 | 192 | 2.37 | -5.33 | -2.96 | 370 | 101 | 248 | 183 |

289 ^{a)}Absorption spectrum was measured in chloroform (CF) solution; ^{b)} Film was prepared by spin-
 290 coating CF solution containing the sample onto glass substrate at a spin speed of 1000 rpm at room
 291 temperature; ^{c)}Emission spectrum was analysed in CF solution; ^{d)}Optical bandgap was calculated from
 292 the formula of $1240/\lambda_{\text{onset}}$; ^{e)}The oxidation potential was also measured by photoelectron spectroscopy
 293 in air (PESA); ^{f)} $E_{\text{LUMO}}^{\text{PESA}} = E_{\text{HOMO}}^{\text{PESA}} + E_g^{\text{opt}}$.

294



295

296 **Fig. 4.** Diagram of the device structure and energy levels in (a) OLED and (b) PSC devices.

297

298 **OLEDs Performance.**

299 Owing to intense luminescence under UV-lamp (both solution and solid state) of
 300 **TPA-NADT-TPA**, **TPA-ANR-TPA**, and **DPA-ANR-DPA**, we decided to investigate them
 301 further in OLED devices using the thin film as an active light-emitting layer. To prove this,
 302 the photoluminescence quantum yield (PLQY) of these compounds was estimated in
 303 chloroform solution and neat thin film. The corresponding data are shown in Table 2. The
 304 same molecules are also studied in PSC devices, which are shown in the next part, in order to
 305 investigate the effect of three different chemical structures on the device performance.

306 For OLED devices, a host-guest layer was introduced because this system has the
 307 benefit of improving electroluminescence and operational stability.⁵⁹ 3 wt% of each **TPA-**
 308 **NADT-TPA**, **TPA-ANR-TPA**, and **DPA-ANR-DPA** materials were doped into a wide-
 309 band-gap host material as an emissive layer in OLED devices, which is illustrated in Fig. 4a.

310 Their use as dopant in a wide band gap host improves hole injection ability and reduces the
311 concentration-quenching effect on emitters. A simple OLED device architecture was
312 fabricated as follows: ITO/HATCN/NPB/MADN: dopant/TPBi/LiF/Al. According to this
313 configuration, 1,4,5,8,9,11-hexaazatriphenylene hexacarbonitrile (HATCN) and 4,4'-bis[*N*-
314 (1-naphthyl)-*N*-phenylamino]biphenyl (NPB) acts as a hole injecting and transporting layers
315 whereas 2-methyl-9,10-bis(naphthalen-2-yl)anthracene (MADN) was used as the host
316 compound with our newly synthesized dopant as a light-emitting layer. Additionally, 1,3,5-
317 tris(*N*-phenyl benzimidazol-2-yl)benzene (TPBi) was used as the hole-blocking or electron-
318 transporting layer whereas LiF was used as electron injecting layer. The chemical structure of
319 all these functional materials was illustrated in Fig. S7 (ESI[†]).

320 The characterization of a series of OLED devices is revealed in Fig. 5 and 6. The
321 relevant data is summarized in Table 2. As shown in Fig. 5, the emission color varies from
322 sky blue (**TPA-NADT-TPA**), blue-green (**TPA-ANR-TPA**) to pure green (**DPA-ANR-**
323 **DPA**). The obtained brightness is indeed very high and promising. The electroluminescence
324 (EL) peaks for **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA** based OLED
325 devices are recorded at 465 nm, 486 nm, and 522 nm with the Commission Internationale de
326 l'Éclairage (CIE) ordinating (0.16, 0.23), (0.17, 0.39), and (0.32, 0.62), respectively.
327 Furthermore, Fig. 6 exhibits the maximum brightness of the devices was 8682 cd/m² for
328 **TPA-NADT-TPA**, 11180 cd/m² for **TPA-ANR-TPA**, and 18600 cd/m² for **DPA-ANR-DPA**
329 respectively. In addition, the power efficiency (PE) for **TPA-NADT-TPA**, **TPA-ANR-TPA**,
330 **DPA-ANR-DPA** based OLED devices is 3.1, 5.9, and 8.0 lumen per watt (lm/W) at 4V,
331 respectively. All the OLED devices exhibit a low turn on voltage close to 3.8 V. The lower
332 voltage is due to an appropriate HOMO energy level. The current efficiency (CE) of **TPA-**
333 **NADT-TPA**, **TPA-ANR-TPA**, **DPA-ANR-DPA** based OLED devices is 4.0, 7.8, and 11.5
334 candela per ampere (cd/A) respectively. Among them, **DPA-ANR-DPA** based devices
335 exhibited higher CE, PE and brightness. Meanwhile, the emission of **TPA-ANR-TPA** results
336 in the blue-green light and its OLEDs shows lowest efficiency, which is due to its more
337 molecular aggregation.⁷⁸ For ANR derivatives, while DPA groups is not as strong electron-
338 donating ability as TPA ones, the CE, PE and maximum brightness of **DPA-ANR-DPA** in
339 OLEDs is higher than those of **TPA-ANR-TPA**. On the other hand, the other ANR-based
340 compound, namely DPA, exhibited pure blue emission in the previous report with brightness
341 up to 6627 cd/m².⁴⁶ In the present study, by replacing two phenyl rings with DPA and TPA
342 units, the brightness increases to 11180 cd/m² for **DPA-ANR-DPA** and 18600 cd/m² for

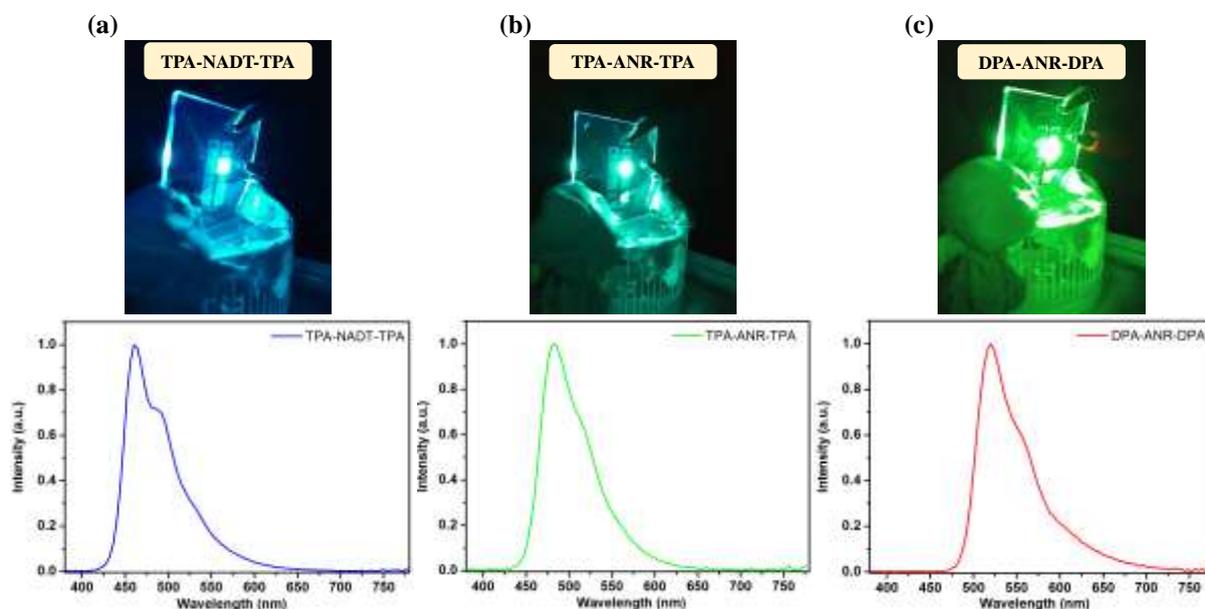
343 **TPA-ANR-TPA**. Also, the emission color diverges from pure blue into pure green (**DPA-**
 344 **ANR-DPA**) and blue-green (**TPA-ANR-TPA**), which indicates that the introduction of
 345 stronger electron donating units has effects on the emission color of ANR derivatives based
 346 OLEDs. The promising performance of all of the newly designed materials in OLED devices
 347 clearly indicates the great potential of acene based organic semiconductors.

348

349 **Table 2.** Performance of OLED device.

| Device | Turn on voltage (V) @ 1 cd/m ² | CE (Cd/A) | PE (lm/W) | CIE (x,y) | EL peak (nm)/FWHM (nm) | Max. brightness (cd/m ²) | PLQY (%) | |
|--------------|---|---------------|------------|------------|------------------------|--------------------------------------|----------|-------|
| | | | | | | | Solution | Film |
| TPA-NADT-TPA | 3.8 | 4 (@6 V) | 3.1 (@4 V) | 0.16, 0.23 | 465/65 | 8682 | 10.89 | 58.49 |
| TPA-ANR-TPA | 3.8 | 7.8 (@6 V) | 5.9 (@4 V) | 0.17, 0.39 | 486/63 | 11180 | 16.20 | 66.98 |
| DPA-ANR-DPA | 3.8 | 11.5 (@4.5 V) | 8 (@4.5 V) | 0.32, 0.62 | 522/61 | 18600 | 18.60 | 6.51 |

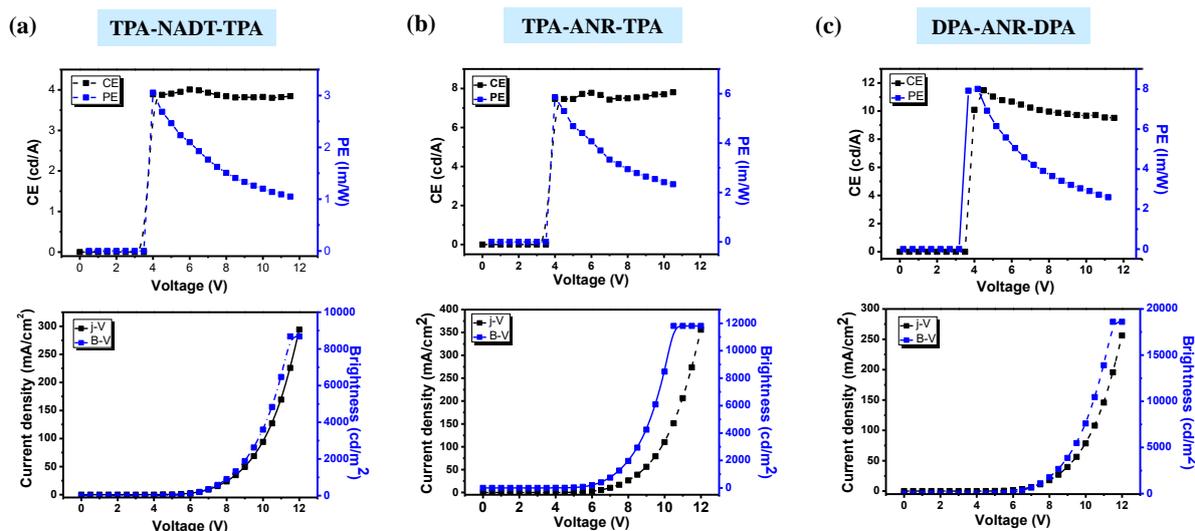
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351

352 **Fig. 5.** Electroluminescent spectrum of OLED with (a) **TPA-NADT-TPA**, (b) **TPA-ANR-**
 353 **TPA** and (c) **DPA-ANR-DPA** dopants in MADN.

354

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356

357 **Fig. 6.** Current efficiency (CE) and current density characteristics of (a) **TPA-NADT-TPA**,
 358 (b) **TPA-ANR-TPA** and (c) **DPA-ANR-DPA** dopants in MADN based OLED devices.

359

360 PSCs Performance.

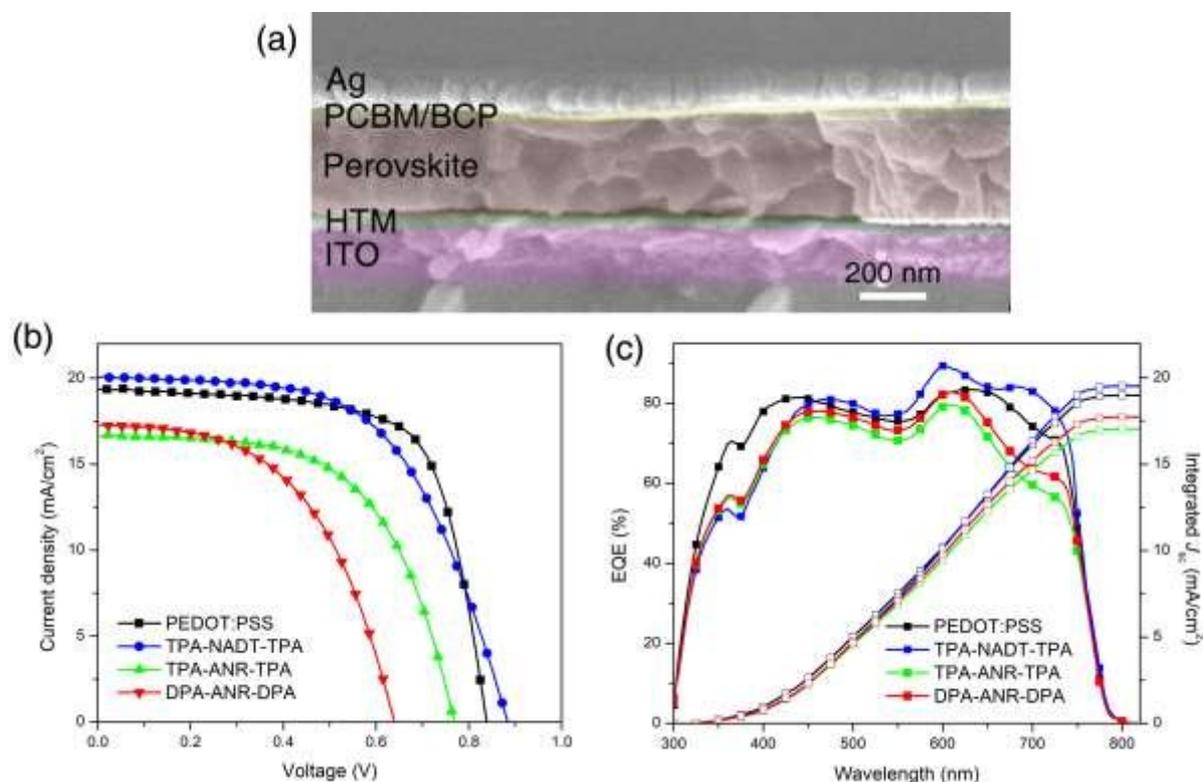
361 Since the molecular design of **TPA-NADT-TPA**, **TPA-ANR-TPA**, and **DPA-ANR-**
 362 **DPA** contains TPA and DPA end-capping groups at the end of the acene cores which
 363 facilitate hole conduction, all these materials could be potential materials for HTL in
 364 perovskite solar cells as suggested by earlier reports.^{25, 36, 53, 62, 79-81} Therefore, these
 365 compounds were implemented in the inverted device layouts:
 366 glass/ITO/HTL/perovskite/PCPM/BCP/Ag as in our previous study.²⁵ In this structure, the
 367 active layer is $\text{CH}_3\text{NH}_3\text{PbI}_3$ whereas 2,9-dimethyl-4,7-diphenyl-1,10-phenanthroline (BCP)
 368 acts as an electron extracting and hole blocking layer and the fullerene derivative [6,6]-
 369 phenyl C61 butyric acid methyl ester (PCBM) as an electron transporting compact layer. The
 370 device construction and energy levels of each layer are illustrated in Fig. 4b. Moreover, the
 371 chemical structure of PCPM and BCP was depicted in Fig. S8 (ESI[†]).

372 The performance of inverted devices based on different HTMs was investigated and
 373 shown in Fig. 7. According to the cross-sectional scanning electron microscopy (SEM) image
 374 of a complete device shown in Fig. 7a, above the indium tin-oxide (ITO) coated glass there is
 375 a thin layer of HTM and the perovskite layer, electron transporting layer (including PCBM
 376 and BCP) and back silver electrode. Fig. 7b presents the current density–voltage (J – V)

377 characteristic measured under simulated sun illumination (AM 1.5 G, 100 mWcm⁻²). The
378 corresponding parameters are listed in Table 3. Overall, the devices based on these new
379 HTMs are found to achieve the PCE of 10.27 % for **TPA-NADT-TPA**, 7.54 % for **TPA-**
380 **ANR-TPA** and 6.05 % for **DPA-ANR-DPA**, compared to that of standard PEDOT:PSS
381 based device (11.29%). The lower efficiency of **TPA-ANR-TPA** and **DPA-ANR-DPA** based
382 devices compared to standard PEDOT:PSS ones may be caused by the aggregation of these
383 chemical structures.⁸² This is related to their low solubility in chlorobenzene/dichlorobenzene,
384 which makes it more challenging to obtain smooth and uniform films. In addition, the devices
385 based on **TPA-NADT-TPA** and PEDOT:PSS HTMs result in a better PCE in comparison
386 with the others because of the presence of thiophene units.^{25, 62} For ANR derivatives, even
387 though **DPA-ANR-DPA** shows a better solubility than **TPA-ANR-TPA**, the device
388 efficiency of **TPA-ANR-TPA** HTL is higher than that with **DPA-ANR-DPA**. This may be
389 attributed to the less strong electron-donating ability of DPA units, leading to a lower hole
390 mobility of the DPA compound.⁴⁷ This result also coincides well with earlier studies
391 reporting that the efficiency achieved using HTMs based on TPA end-capping groups is
392 greater than that with DPA under similar conditions in inverted⁸³ and mesoporous^{47, 84-87}
393 configurations.

394 According to Table 3, the devices with **TPA-NADT-TPA** HTL present a better open-
395 circuit voltage (V_{oc}) than that with PEDOT:PSS, demonstrating a better band alignment of
396 **TPA-NADT-TPA** HTL with the perovskite layer. Although the HOMO values of **TPA-**
397 **ANR-TPA** and **DPA-ANR-DPA** are close to that of perovskite materials, their V_{oc} values are
398 not better than that of **TPA-NADT-TPA**. This may be triggered by the poor uniformity of
399 these materials⁸⁸ and high interfacial recombination in the devices,^{89, 90} leading to the low
400 efficiency of ANR derivatives. Additionally, the short-circuit current (J_{sc}) for **TPA-NADT-**
401 **TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA** are 20.04, 16.68, and 17.49 mA cm⁻²,
402 respectively. These values also match well with the values obtained from the integrated
403 external quantum efficiency (EQE) spectra (as shown in Fig. 7c). While the J_{sc} of **TPA-**
404 **NADT-TPA** HTL based devices is better than that of standard PEDOT:PSS HTL, the devices
405 with **TPA-NADT-TPA** HTL exhibit a lower PCE than those using PEDOT:PSS HTL. The
406 reason is due to the significant drop in fill factor (FF) of **TPA-NADT-TPA**, which may be
407 caused by a less smooth film and lower mobility of this new material.^{88, 91} The series
408 resistance (R_s) for the four HTL-based devices was derived from the J - V curves according to
409 the previous report.⁹² The PEDOT:PSS based PSC shows a low R_s value of 5.36 Ω ·cm², while

410 the **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA** based PSCs show higher R_s of
 411 $10.68 \Omega\text{-cm}^2$, $8.52 \Omega\text{-cm}^2$ and $9.43 \Omega\text{-cm}^2$. The higher R_s for the three new HTL resulted in
 412 lower FF and subsequently limited the PCE.⁹²



413
 414 **Fig. 7.** a) Cross-sectional scanning electron microscopy image of the device, b) Current
 415 density–voltage curves (J - V) of PSCs with different HTMs, and c) their external quantum
 416 efficiency (EQE) spectra (lines with open symbols indicate the integrated J_{sc} from EQE and
 417 solar spectrum).

418

419 **Table 3.** J - V parameters of PSCs with different HTLs as **TPA-NADT-TPA**, **TPA-ANR-**
 420 **TPA** and **DPA-ANR-DPA** and PEDOT:PSS.^{a)}

| HTLs | V_{OC} [V] | J_{SC} [mA/cm^2] | FF | PCE ^{b)} [%] |
|--------------|--------------|--------------------------------------|-------|-----------------------|
| PEDOT:PSS | 0.83 | 19.38 | 0.70 | 11.29 |
| TPA-NADT-TPA | 0.88 | 20.04 | 0.58 | 10.27 |
| TPA-ANR-TPA | 0.77 | 16.68 | 0.589 | 7.54 |
| DPA-ANR-DPA | 0.63 | 17.49 | 0.549 | 6.05 |

421 ^a)Cell size (active area): 7 mm². Photovoltaic performance at 1000 w m⁻² (AM1.5G) and
422 constant scan speed of 30 mV/s mesoscopic CH₃NH₃PbI₃ devices; ^b)An average device
423 efficiency of total 10 devices.

424

425 CONCLUSIONS

426 In summary, we have designed and developed a novel series of acene based solution
427 processable organic semiconductors with triphenylamine and diphenylamine end capping
428 groups. The compounds namely 2,7-bis(trimethylstannyl)naphtho[2,1-*b*:6,5-*b'*]dithiophene
429 (**TPA-NADT-TPA**), 4,4'-(anthracene-2,6-diyl)bis(*N,N*-bis(4-methoxyphenyl)aniline (**TPA-
430 ANR-TPA**), and *N*²,*N*²,*N*⁶,*N*⁶-tetrakis(4-methoxyphenyl)anthracene-2,6-diamine (**DPA-
431 ANR-DPA**) were synthesized by Stille, Suzuki, and Buchwald organometallic coupling. The
432 effect of central acene cores varying from lower conjugation anthracene to highly extended
433 conjugated naphthodithiophene attached to end capping triphenyl and diphenyl amine moiety
434 on the opto-electronic properties were studied. The optical band gap is in the range of 2.3 to
435 2.7 eV, placing these newly compounds in the area of wide band gap compounds.
436 Interestingly, these materials, which possess suitable LUMO-HOMO energy levels, can play
437 dual functionality in OLEDs and PSCs. For OLED devices based on these materials, their
438 electroluminescence maximum varies in the range of 465 nm to 522 nm with sky-blue, blue-
439 green to pure green thin film colour emission. Additionally, they exhibit a low turn-on
440 voltage at 3.8 V and strong emission with the maximum brightness of 8682 cd/m² for **TPA-
441 NADT-TPA**, 11180 cd/m² for **TPA-ANR-TPA**, and 18600 cd/m² for **DPA-ANR-DPA**.
442 These small molecules have been also fabricated successfully in perovskite solar cell devices
443 as HTMs without additives. The inverted devices based on these HTMs achieve an overall
444 efficiency of 10.27 % for **TPA-NADT-TPA**, 7.54 % for **TPA-ANR-TPA** and 6.05 % for
445 **DPA-ANR-DPA**. The excellent performance of these newly designed materials, in both
446 OLED and PSC devices, confirms that our innovative molecular design of organic
447 semiconductors is a promising and versatile approach. These materials play a dual role and
448 this opens up a new research strategy where single materials can be used for multiple devices.

449

450 EXPERIMENTAL SECTION

451 1. Synthesis

452 The synthesis of compound (2) and (3) was followed an earlier published synthetic procedure.^{25, 39}

454 Synthesis of 2,7-Bis(trimethylstannyl)naphtho[1,2-b:5,6-b']dithiophene (5): n-Butyllithium
455 (2.4 M solution in hexane, 3.03 mL, 7.28 mmol) was added dropwise to a solution of
456 compound (4) (500 mg, 2.08 mmol) in dry THF (50 mL) at -78 °C. The mixture was stirred at
457 this temperature for 30 min and then at room temperature for 1 h. After cooling down to -78
458 °C, Me₃SnCl (1 M solution in hexane, 8.32 mL, 8.32 mmol) was added dropwise. After
459 stirring for 30 min at this temperature, the reaction was allowed to warm up to room
460 temperature and stirred overnight. The reaction mixture was then extracted with chloroform
461 and water. The organic layer was dried over anhydrous Na₂SO₄ and concentrated by
462 evaporation. After removing the solvent under reduced pressure, the residue was purified by
463 recrystallization from acetone (800 mg, 69 %). ¹H NMR (600 MHz, CDCl₃): 7.98-7.96 (d,
464 2H), 7.84-7.83 (d, 2H), 7.48 (s, 2H), 0.39 (s, 18H).

465 Synthesis of 2,7-bis(trimethylstannyl)naphtho[2,1-b:6,5-b']dithiophene (TPA-NADT-TPA):
466 Compound (5) (350 mg, 0.616 mmol) and compound (2) (640 mg, 0.166 mmol) were
467 vacuumed for 20 minutes prior to adding anhydrous DMF (35 ml). The solution was
468 degassed with argon for 20 minutes and then tetrakis (triphenylphosphine) palladium (25 mg,
469 0.022 mmol) was added. The reaction was refluxed at 110 °C for 48 hours then extracted by
470 chloroform. The extract was dried and concentrated. The purification of the residue on silica
471 using hexane : dichloromethane (2:1 v/v) as the eluent. It was recrystallized by hot methanol
472 to yield the desired compound as a yellow solid (200 mg, 38.4 %). ¹H NMR (600 MHz,
473 CDCl₃): δ 7.89-7.88 (d, *J* = 8.4 Hz, 2H), 7.75-7.74 (d, *J* = 8.4 Hz, 2H), 7.50-7.43 (m, 6H),
474 7.02 (s, 8H), 6.88 (s, 4H), 6.79-6.78 (d, *J* = 9.0 Hz, 8H), 3.74 (s, 12H). ¹³C NMR (120 MHz,
475 CDCl₃): δ 156.26, 149.30, 143.51, 140.27, 138.28, 137.38, 130.53, 126.97, 125.62, 122.35,
476 121.21, 120.35, 119.07, 118.18, 114.73, 55.52. ESI-MS: C₅₄H₄₂N₂O₄S₂⁺ *m/z* 846.33
477 (calculated *m/z* 846.26).

478 Synthesis of 4,4'-(anthracene-2,6-diyl)bis(*N,N*-bis(4-methoxyphenyl)aniline (TPA-ANR-TPA):
479 In a round bottom flask, compound (5) (200 mg, 0.599 mmol), compound (4) (723 mg,
480 1.677 mmol), and 2 M aqueous K₂CO₃ solution (12 mL) were dissolved in anhydrous toluene
481 (20 mL). The solution was degassed by argon for 20 minutes, then
482 tetrakis(triphenylphosphine)palladium (21 mg, 0.018 mmol) was added. Subsequently, the
483 mixture was degassed for 30 min before the reaction was stirred at 120 °C for 2 days. After

484 the reaction mixture was cooled to room temperature and extracted with chloroform and
485 water. The organic layer was dried over anhydrous Na_2SO_4 . After removing the solvent under
486 reduced pressure, the residue was purified using silica gel column chromatography with a
487 mixture of hexane, chloroform, and ethyl acetate as eluent. Then the crude product was
488 recrystallized from hot methanol to yield the desired compound as a yellow solid (180 mg,
489 38.3%). ^1H NMR (600 MHz, CDCl_3): δ 8.33 (s, 2H), 8.05 (s, 2H), 7.96-7.94 (d, $J = 9$ Hz,
490 2H), 7.66-7.64 (dd, $J = 1.8, 10.2$ Hz, 2H), 7.53-7.52 (d, $J = 8.4$ Hz, 4H), 7.05-7.04 (d, $J = 9$
491 Hz, 8H), 6.98-6.97 (d, $J = 8.4$ Hz, 4H), 6.80-6.78 (m, 8H), 3.74 (s, 12H). ^{13}C NMR
492 (120 MHz, CDCl_3): δ 155.96, 140.84, 137.18, 132.73, 131.97, 131.05, 128.53, 127.68,
493 126.69, 125.93, 125.37, 124.35, 120.78, 114.74, 55.52. ESI-MS: $\text{C}_{54}\text{H}_{44}\text{N}_2\text{O}_4^{+}$ m/z 784.50
494 (calculated m/z 784.33).

495 Synthesis of 4,4'-(anthracene-2,6-diyl)bis(*N,N*-bis(4-methoxyphenyl)aniline (DPA-ANR-

496 **DPA**): Compound (6) (200 mg, 0.599 mmol), bis(4-methoxyphenyl)amine (343 mg, 1.497
497 mmol), and NaO^tBu (149 mg, 1.797 mmol) were added and vacuumed for 30 min.
498 Afterwards, anhydrous toluene (25 ml) and $^t\text{Bu}_3\text{P}$ (1M toluene solution, 20 μl , 0.02 mmol)
499 were added to dissolve the solid and degassed by argon for 30 min. Then, $\text{Pd}_2(\text{dba})_3$ (22.2 mg,
500 0.024 mmol) was added and the mixture was vacuumed and degassed for 30 min.
501 Subsequently, the reaction was stirred at 110 $^\circ\text{C}$ for 2 days. After the reaction mixture was
502 cooled to room temperature and extracted with chloroform and water. The organic layer was
503 dried over anhydrous Na_2SO_4 and the solvent removed under reduced pressure. The residue
504 was purified using silica gel column chromatography with a mixture of hexane and
505 chloroform as eluent. Then the crude product was recrystallized from hot methanol to yield
506 the desired compound as a yellow solid (190 mg, 50.2 %). ^1H NMR (600 MHz, CDCl_3): δ
507 7.94 (s, 2H), 7.69-7.68 (d, $J = 9$, 2H), 7.25 (s, 2H), 7.19-7.18 (dd, $J = 1.8, 9$ Hz, 2H), 7.13-
508 7.12 (d, $J = 9$ Hz, 8H), 6.88-6.87 (d, $J = 9$ Hz, 8H), 6.80-6.78 (m, 8H), 3.84 (s, 12H). ^{13}C
509 NMR (120 MHz, CDCl_3): δ 155.81, 144.92, 141.11, 131.55, 128.98, 128.30, 126.84, 126.41,
510 123.69, 115.27, 114.67, 55.52. ESI-MS: $\text{C}_{42}\text{H}_{36}\text{N}_2\text{O}_4^{+}$ m/z 632.42 (calculated m/z 632.27).

511

512 2. OLED Device Fabrication

513 OLED devices based on **TPA-NADT-TPA**, **TPA-ANR-TPA** and **DPA-ANR-DPA** were
514 fabricated by thermal evaporation. The three synthesized materials were used as dopants with
515 device configuration of: ITO/HATCN (10 nm)/NPB (45 nm)/MADN: 3 wt% dopant (35

516 nm)/TPBi (35 nm)/LiF (1 nm)/Al (150 nm). In this configuration, 1,4,5,8,9,11-
517 hexaazatriphenylene hexacarbonitrile (HATCN) and 4,4'-bis[N-(1-naphthyl)-N-
518 phenylamino]biphenyl (NPB) act as a hole injecting and transporting layers, respectively.
519 Additionally, while 2-methyl-9,10-bis(naphthalen-2-yl)anthracene (MADN) was used as the
520 host compound, 1,3,5-tris(N-phenyl benzimidazol-2-yl)benzene (TPBi) was used as the
521 electron-transporting layer. Furthermore, LiF and Al were used as the electron injecting layer
522 and cathode, respectively. All organic and inorganic layers were deposited onto the UV
523 ozone treated ITO glass substrates in a multiple thermal source vacuum deposition chamber
524 under 2×10^{-6} Torr. The device electroluminescent performances such as current-voltage,
525 brightness, electroluminescent spectra, C.I.E co-ordinates were measured and recorded by a
526 computer-controlled DC power supply with a Spectra PR650 CCD camera.

527

528 3. Perovskite Device Fabrication

529 Poly(3,4-ethylenedioxythiophene) polystyrene sulfonate (PEDOT:PSS, AI 4083) and
530 bathocuproine (BCP) were purchased from Heraeus and Lumtec, respectively. PbI₂ was
531 purchased from TCI (Tokyo Chemical Industry). Other chemicals were purchased from
532 Sigma-Aldrich. PCBM (60) was purchased from Nano-C. Methylammonium iodide (MAI)
533 was synthesized according to a previously reported method. The perovskite precursor
534 solution (MAPbI₃) was prepared by dissolving MAI and PbI₂ with stoichiometric ratio in
535 gammabutyrolactone/dimethyl sulfoxide (7:3 v/v, 1.1 M) at 80°C.

536 Perovskite solar cells were prepared on a pre-cleaned patterned ITO substrate. A filtered
537 PEDOT:PSS solution was spin-coated on ITO at 3000 rpm and annealed at 150°C for 10 min.
538 For new HTMs (**TPA-NADT-TPA**, **TPA-ANR-TPA**, and **DPA-ANR-DPA**) based devices,
539 while **TPA-ANR-TPA** was prepared with a mixed solvent of chloroform and 1,2-
540 dichlorobenzene at 2 mg/ml (1:1 v/v), **TPA-NADT-TPA** and **DPA-ANR-DPA** were
541 dissolved in 1,2-dichlorobenzene at 5 mg/ml. Afterwards, they were spin-coated on the ITO
542 substrate. The film thickness was varied by changing the spin speed from 2000 rpm to 5000
543 rpm. The perovskite precursor solution (pre-heated at 80°C) was spin-coated onto these hole-
544 transporting layers at 1000 rpm for 10 s and 4000 rpm for 30 s, 250 μ L toluene was dripped
545 on the sample surface at 15 s of the second step spin-coating. Subsequently, the perovskite
546 layer was annealed at 80°C for 5 min, 100°C for 30 min. The PCBM solution was coated
547 from a chlorobenzene solution (20 mg/mL) at 1000 rpm for 60 s. The devices were completed

548 by evaporating BCP (6 nm) and Ag (120 nm) sequentially under high vacuum (1×10^{-6} mbar).
549 The active area was 7 mm² as defined by the overlapping between the back electrode and ITO.
550 Current density-voltage (*J-V*) characteristics were measured using a calibrated solar simulator
551 (AAA, SAN-EI ELECTRIC CO.,LTD.) coupled with Keithley 2400 Source meter. External
552 quantum efficiency (EQE) was obtained by combining a monochromatic light source, a light
553 chopper and a lock-in amplifier (SR830-DSP).

554

555 AUTHOR INFORMATION

556 Corresponding Author

557 *E-mail: sonar.prashant@qut.edu.au.

558 Author Contributions

559 The manuscript was written through contributions of all authors. All authors have given
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561

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570

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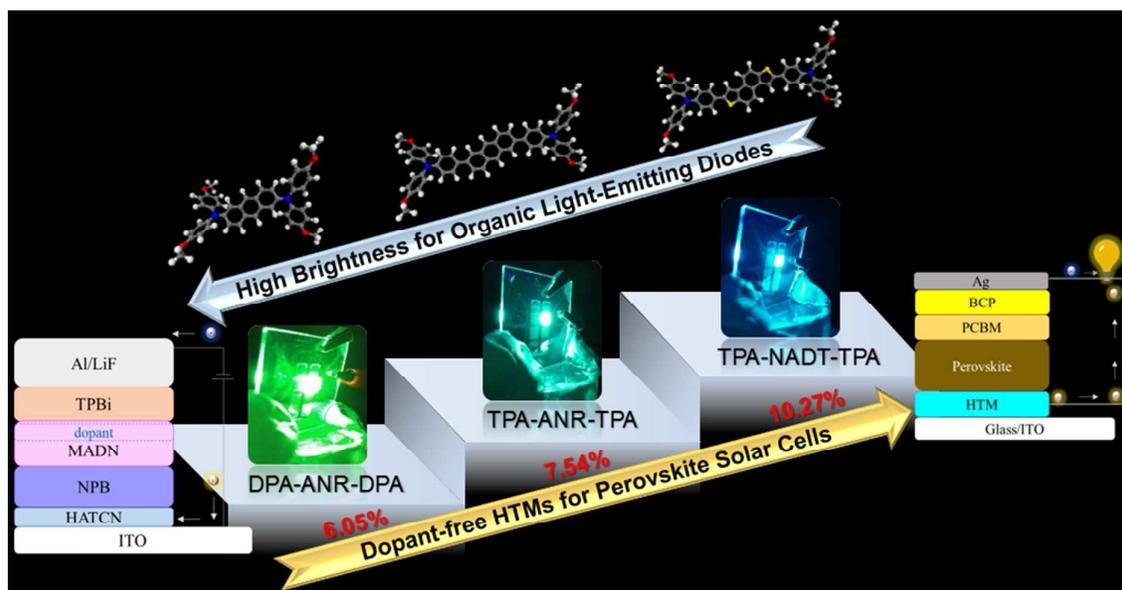
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TOC graph



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A series of strong electron-rich small molecules based acene were designed and synthesized for the purpose of green/blue organic light-emitting diodes and perovskite solar cells applications.

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